Silicon NPN Epitaxial



ADE-208-004 1st. Edition

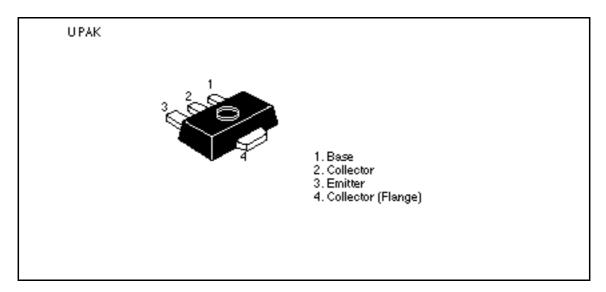
Application

VHF / UHF wide band amplifier

Features

- High gain bandwidth product $f_T = 8.5$ GHz Typ
- High gain, low noise figure PG = 10.5 dB Typ, NF = 1.3 dB Typ at f = 900 MHz

Outline





<u>2SC4988</u>

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	15	V
Collector to emitter voltage	V _{CEO}	9	V
Emitter to base voltage	V _{EBO}	1.5	V
Collector current	Ι _c	100	mA
Collector power dissipation	Pc	800*1	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. This value is allowed when using the alumina ceramics board (12.5 x 20 x 0.7 mm)

Electrical Characteristics (Ta = 25°C)

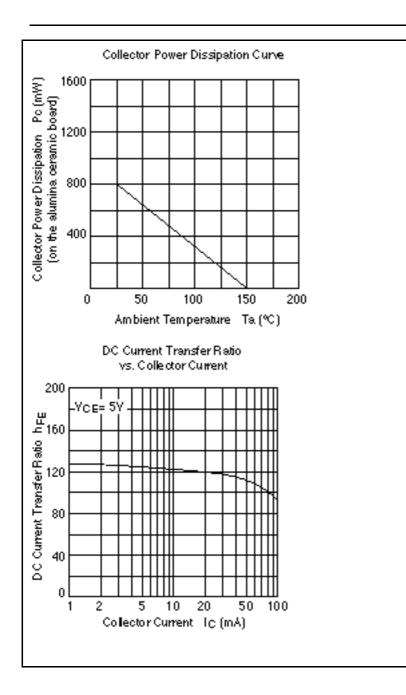
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}		_	1	μA	$V_{CB} = 12 \text{ V}, \text{ I}_{E} = 0$
	I _{CEO}	_	_	1	mA	$V_{ce} = 9 V, R_{be} =$
Emitter cutoff current	I _{EBO}	_	_	10	μA	$V_{EB} = 1.5 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE}	50	120	250		$V_{ce} = 5 \text{ V}, I_c = 20 \text{ mA}$
Collector output capacitance	Cob	_	1.1	1.6	pF	$V_{_{CB}} = 5 \text{ V}, I_{_{E}} = 0, f = 1 \text{ MHz}$
Gain bandwidth product	f _T	5.5	8.5	_	GHz	$V_{ce} = 5 \text{ V}, I_c = 20 \text{ mA}$
Power gain	PG	7.5	10.5	—	dB	V_{ce} = 5 V, I _c = 20 mA, f = 900 MHz
Noise figure	NF	_	1.3	2.5	dB	V_{ce} = 5 V, I _c = 5 mA, f = 900 MHz

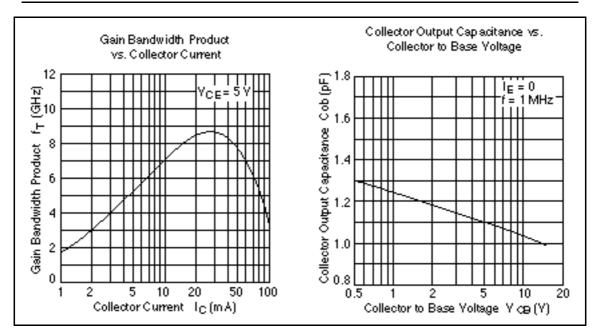
Note: Marking is "FR".

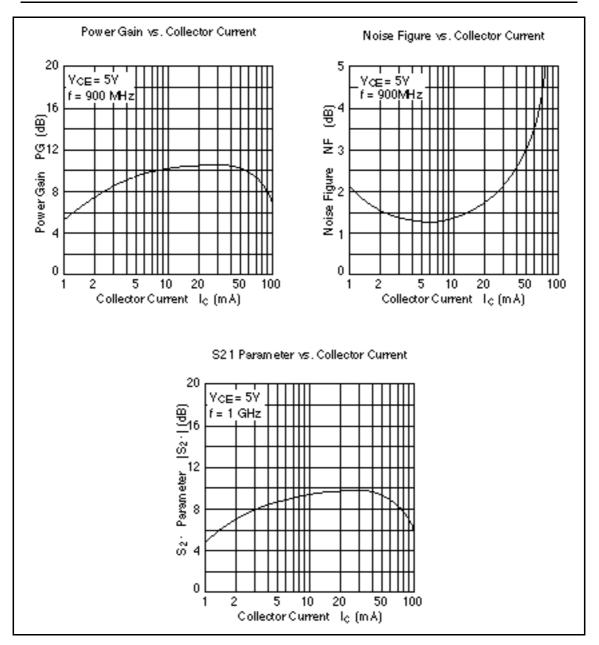
Attention: This device is very sensitive to electro static discharge.

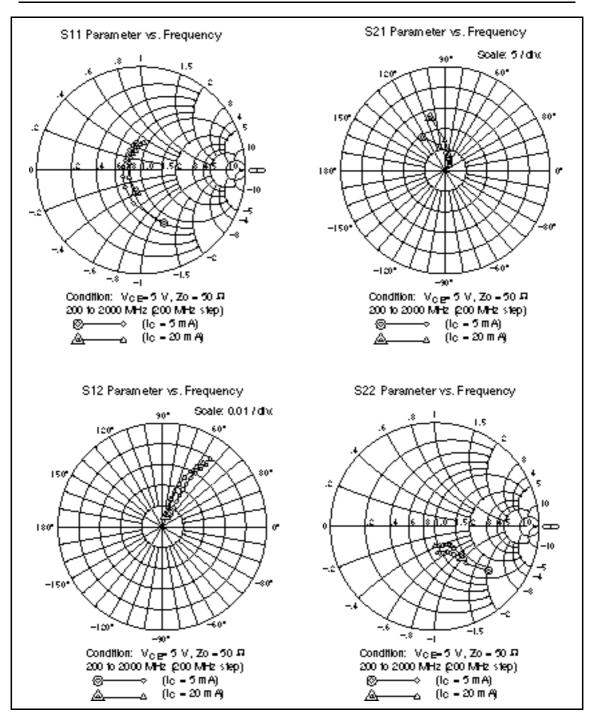
It is recommended to adopt appropriate cautions when handling this transistor.

2<u>SC4988</u>









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Freq. S11			S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.555	-66.6	9.68	124.7	0.0717	62.3	0.672	-39.7
400	0.328	-102.5	5.98	102.2	0.106	59.4	0.462	-49.8
600	0.225	-133.1	4.24	89.3	0.138	60.8	0.371	-53.4
800	0.185	-160.5	3.31	80.3	0.170	61.4	0.326	-56.4
1000	0.172	170.5	2.71	72.4	0.204	61.3	0.301	-59.9
1200	0.179	148.5	2.34	65.8	0.237	60.7	0.285	-63.6
1400	0.200	131.7	2.06	59.9	0.270	59.5	0.276	-68.2
1600	0.224	120.0	1.86	54.4	0.303	58.1	0.268	-73.2
1800	0.253	108.7	1.71	49.6	0.334	56.4	0.262	-78.7
2000	0.277	99.8	1.58	44.9	0.365	54.5	0.256	-84.7

S Parameter (V $_{\rm CE}$ = 5 V, $I_{\rm C}$ = 5 mA, $Z_{\rm O}$ = 50 $\,$)

S Parameter (V $_{CE}$ = 5 V, I_{C} = 20 mA, Z_{O} = 50 $\,$)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.220	-101.8	13.13	106.0	0.0532	71.5	0.401	-48.6
400	0.135	-149.0	7.08	90.8	0.0946	73.6	0.277	-49.0
600	0.120	175.1	4.83	82.2	0.137	72.6	0.239	-50.1
800	0.132	148.0	3.70	75.5	0.178	70.8	0.221	-53.4
1000	0.155	129.6	3.02	69.5	0.220	68.2	0.212	-57.9
1200	0.174	117.3	2.58	63.9	0.258	65.6	0.205	-63.1
1400	0.196	105.5	2.26	58.8	0.296	62.9	0.201	-69.1
1600	0.225	97.8	2.04	54.1	0.331	60.3	0.197	-75.7
1800	0.246	92.0	1.86	50.0	0.364	57.5	0.193	-82.1
2000	0.267	84.5	1.72	45.7	0.397	54.7	0.190	-89.4

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